PST KP2000-26

HIGH POWER PHASE CONTROL THYRISTOR
FOR PHASE CONTROL APPLICATIONS

Features :

- Blocking Capability up to 2600 V
- High dV/dt Capability
- All Diffused Structure
- Amplifying Gate Configuration
- Rugged Ceramic Hermetic Package

ELECTRICAL CHARACTERISTICS AND RATINGS

Blocking

Parameter	Symbol	Min	Max	Typ	Unit	Conditions
Repetitive peak reverse voltage	V_{RRM}		2600		V	Tj = -40 °C to 125 °C
Repetitive peak off-state voltage	V_{DRM}		2600		V	Tj = -40 °C to 125 °C
Non repetitive peak reverse voltage	V_{RSM}		2700		V	Tj = -40 °C to 125 °C
Repetitive peak reverse current	I_{RRM}		200		mA	Tj = Tjmax , V = V_{RRM}
Repetitive peak off-state current	I_{DRM}		200		mA	Tj = Tjmax ,V = V_{DRM}

Conducting

Parameter	Symbol	Min	Max	Typ	Unit	Conditions
Average value of on-state current	$I_{T(AV)}$		2685		A	50 Hz sine wave,180° conduction, T_c = 85 °C
RMS value of on-state current	$I_{T(RMS)}$		4215		A	50 Hz sine wave,180° conduction, T_c = 85 °C
Surge non repetitive current	I_{TSM}		50		kA	50 Hz sine wave Half cycle
I square t	I^2t		12500		kA^2s	V_R = 0 T_j = 125 °C
Peak on-state voltage	V_{TM}		1.21		V	On-state current 2500 A, Tj= Tjmax
Threshold voltage	$V_{T(TO)}$		0.88		V	$T_j = T_{jmax}$
On-state slope resistance	r_T		0.131		mΩ	$T_j = T_{jmax}$
Holding current	I_H			300	mA	V_D = 24 V; I_T = 2.5 A
Latching current	I_L			1500	mA	V_D = 24 V; R_L = 12 Ω

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Triggering

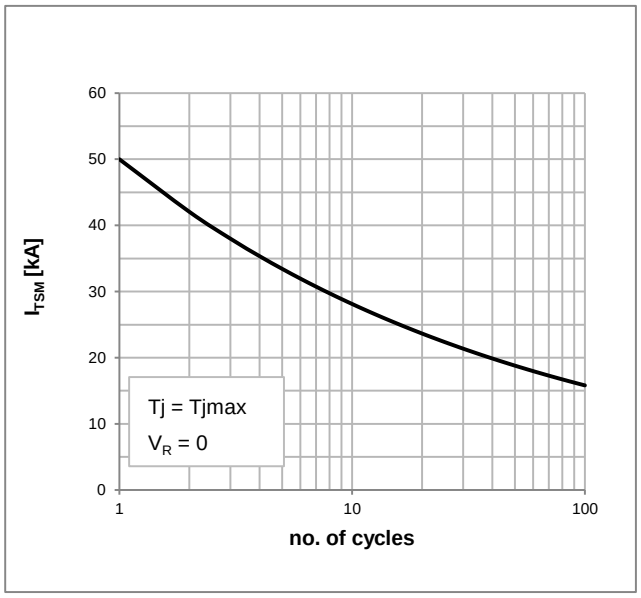
Parameter	Symbol	Min	Max	Typ	Unit	Conditions
Gate current	I_{GT}		500		mA	V_D = 6 V; R_L = 3 Ω; Tj = - 40 °C
			300		mA	V_D = 6 V; R_L = 3 Ω; Tj = 25 °C
			200		mA	V_D = 6 V; R_L = 3 Ω; Tj = 125 °C
Gate voltage	V_{GT}		5		V	V_D = 6 V; R_L = 3 Ω; Tj = - 40 °C
			3		V	V_D = 6 V; R_L = 3 Ω; Tj = 0 ÷ 125 °C
		0.4			V	V_D = V_{DRM}; R_L = 10 kΩ; Tj = 125 °C
Peak gate current	I_{GM}		10		A	
Peak reverse gate voltage	V_{RGM}		5		V	
Peak gate power dissipation	P_{GM}		200		W	
Average gate power dissipation	$P_{G(AV)}$		5		W	

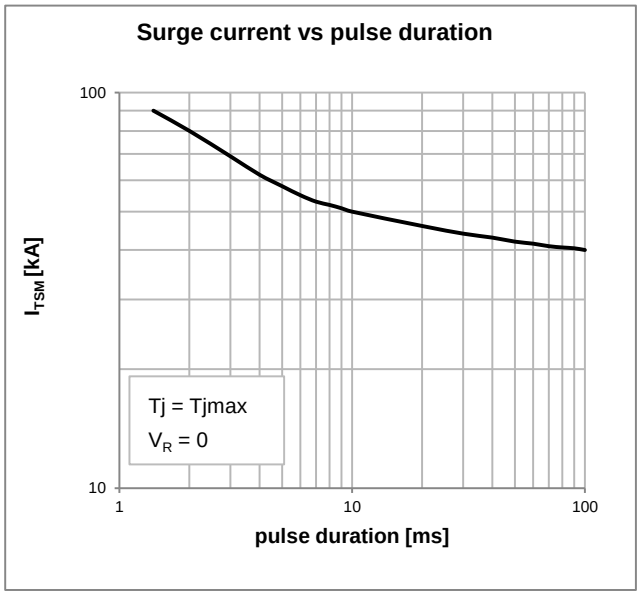
Switching

Parameter	Symbol	Min	Max	Typ	Unit	Conditions
Critical rate of rise of on-state current	**di/dt**		200		A/µs	Switching from $V_{DRM} \leq$ 1000 V - repetitive
Critical rate of rise of on-state voltage	**dv/dt**		1000		V/µs	Linear ramp up to 80% of V_{DRM}
Gate controlled delay time	t_d		2.5		µs	I_{TM} = 50 A; V_D = 1500 V; V_G = 20 V R_G = 20 Ω; t_r = 0.1 µs; t_p = 20 µs
Turn-off time	t_q		500		µs	I_{TM} = 2500 A; di/dt = 25 A/µs;$V_R \geq$ 50 V dV/dt = 50 V/µs linear to 80% V_{DRM} V_G = 0 V;Tj = 125 °C
Reverse recovery charge	Q_{rr}			4600	µC	I_T = 2000 A di/dt = 20 A/µs
Reverse recovery current	I_{rr}			230	A/µs	$V_R \geq$ 50 V T_j = T_{jmax}

Thermal and mechanical

Parameter	Symbol	Min	Max	Typ	Unit	Conditions
Operating temperature	T_j	-40	125		°C	
Storage temperature	T_{stg}	-40	125		°C	
Thermal resistance junction to case	$R_{th(j-c)}$		0.009		°C/W	Double side cooled , DC
Thermal resistance case to sink	$R_{th(c-s)}$		0.002		°C/W	Double side cooled, mounting surfaces smooth, flat and greased
Mounting force	**F**	40	50		kN	
Weight	**W**			1500	g	


60
50
40
30
20
10
0
I_{TSM} [kA]
Tj = Tjmax
V_R = 0
1
10
100
no. of cycles


Surge current vs pulse duration
100
10
I_{TSM} [kA]
Tj = Tjmax
V_R = 0
1
10
100
pulse duration [ms]

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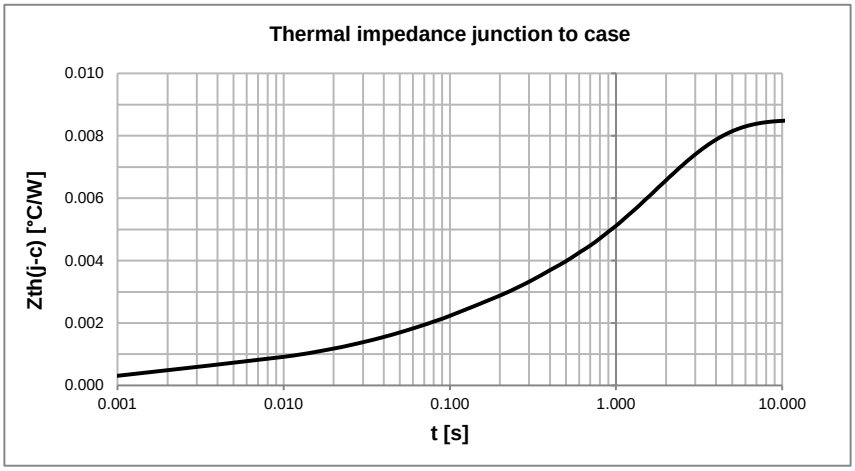
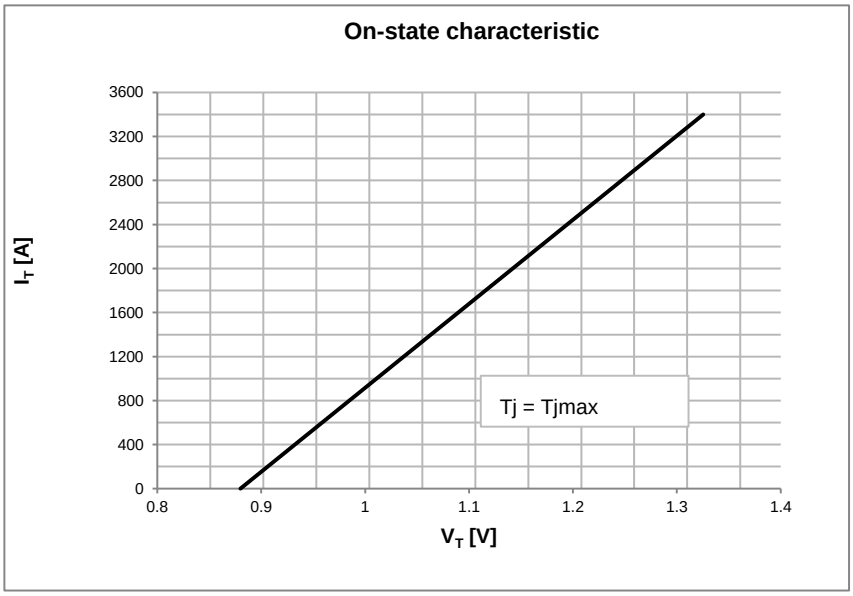
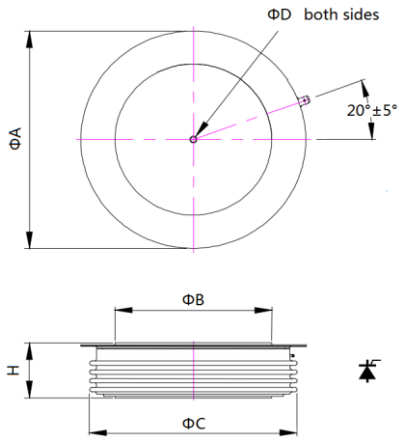




OUTLINE AND DIMENSIONS



	A	B	C	D	H
mm	109	73	98	3.5 x 3	26+/-1

- All the characteristics given in this data sheet are guaranteed only with uniform clamping force, cleaned and lubricated heatsink surfaces with flatness < 0.03 mm and roughness < 2µm